TEXAS INSTRUMENTS
CD54HC166, CD54HCT166, CD74HC166, CD74HCT166
ZHCSPZ5D – FEBRUARY 1998 – REVISED FEBRUARY 2022

CDx4HC(T)166 高速 CMOS 逻辑 8 位并行输入/串行输出移位寄存器

1 特性

- 缓冲输入
- 扇出（在温度范围内）
  - 标准输出：10 个 LSTTL 负载
  - 总线驱动器输出：15 个 LSTTL 负载
- 宽工作温度范围：-55℃ 至 125℃
- 平衡的传播延迟时间及转换时间
- 与 LSTTL 逻辑 IC 相比，功耗显著降低
- HC 类型
  - 2 V 至 6 V 工作电压
  - 高抗噪性：当 V_{CC} = 5 V 时，N_{IL} = 30%，N_{IH} = V_{CC} 的 30%
- HCT 类型
  - 4.5 V 至 5.5 V 工作电压
  - 直接 LSTTL 输入逻辑兼容性，V_{IL} = 0.8V（最大值），V_{IH} = 2V（最小值）

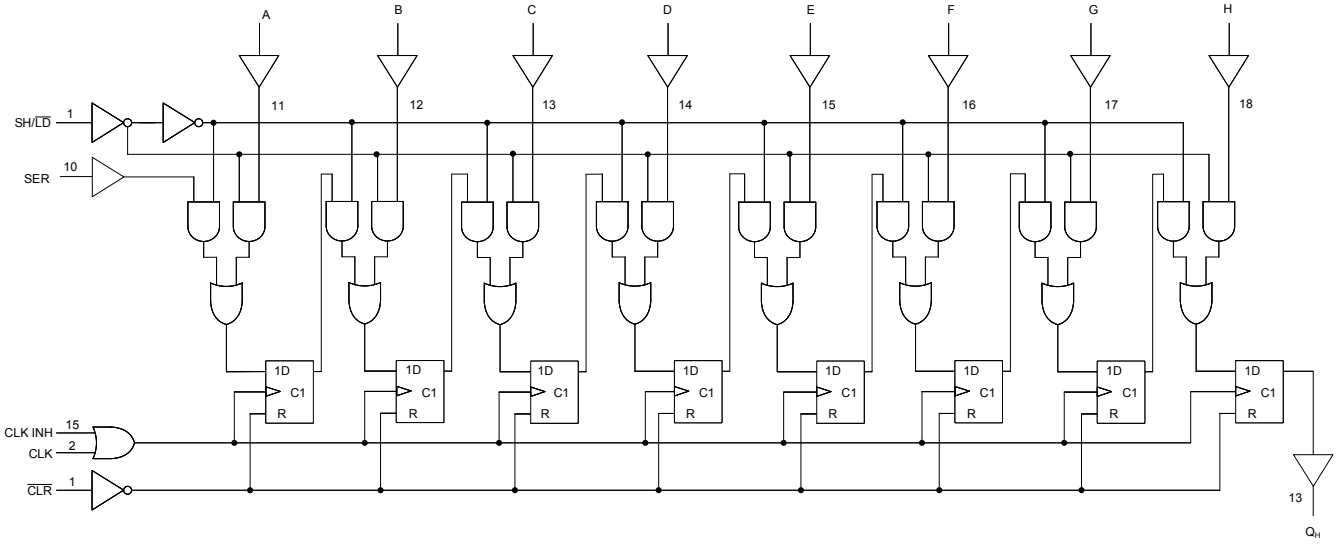
2 说明

HC166 和 HCT166 8 位移位寄存器采用硅栅 CMOS 技术制造。该器件具有标准 CMOS 集成电路的低功耗特性，并可在与等效低功耗肖特基器件相当的速度下运行。

器件信息

器件型号	封装(1)	封装尺寸（标称值）
CD54HC166F3A	CDIP (16)	24.38mm × 6.92mm
CD54HCT166F3A	CDIP (16)	24.38mm × 6.92mm
CD74HC166M	SOIC (16)	9.90mm × 3.90mm
CD74HCT166M	SOIC (16)	9.90mm × 3.90mm
CD74HC166E	PDIP (16)	19.31mm × 6.35mm
CD74HCT166E	PDIP (16)	19.31mm × 6.35mm

(1) 如需了解所有可用封装，请参阅数据表末尾的可订购产品附录。



功能图

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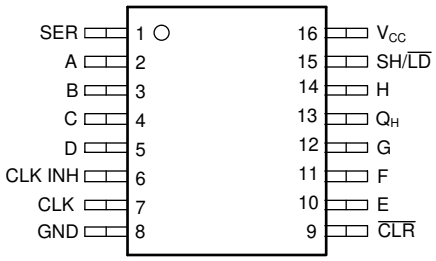
3 Revision History

注：以前版本的页码可能与当前版本的页码不同

Changes from Revision C (October 2003) to Revision D (February 2022)	Page
• 更新了整个文档中的编号、格式、表格、图和交叉参考，以反映现代数据表标准	1

4 Pin Configuration and Functions



J, N, or D package
16-Pin CDIP, PDIP, or SOIC
Top View

5 Specifications

5.1 Absolute Maximum Ratings(1)

			MIN	MAX	UNIT
V_{CC}	Supply voltage		–0.5	7	V
I_{IK}	Input diode current	For V_I < -0.5 V or V_I > VCC + 0.5 V		±20	mA
I_{OK}	Output diode current	For V_O < -0.5 V or V_O > V_{CC} + 0.5 V		±20	mA
I_O	Drain current, per output	For -0.5 V < V_O < V_{CC} + 0.5 V		±25	mA
I_O	Output source or sink current per output pin	For V_O > -0.5 V or V_O < V_{CC} + 0.5 V		±25	mA
	Continuous current through V_{CC} or GND			±50	mA
T_J	Junction temperature			150	°C
T_{stg}	Storage temperature range		-65	150	°C
	Lead temperature (Soldering 10s)(SOIC - lead tips only)			300	°C

(1) Stresses beyond those listed under *absolute maximum ratings* may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions beyond those indicated under *recommended operating conditions* is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

5.2 Recommended Operating Conditions

			MIN	MAX	UNIT
V_{CC}	Supply voltage range	HC Types	2	6	V
		HCT Types	4.5	5.5	V
V_I, V_O	Input or output voltage		0	V_{CC}	V
t_t	Input rise and fall time	2V		1000	ns
		4.5V		500	
		6V		400	
T_A	Temperature range		–55	125	℃

5.3 Thermal Information

THERMAL METRIC		D (SOIC) 16 PINS	N (PDIP) 16 PINS	UNIT
$R_{\theta JA}$	Junction-to-ambient thermal resistance(1)	73	67	°C/W

(1) For more information about traditional and new thermal metrics, see the *Semiconductor and IC package thermal metrics* application report.

5.4 Electrical Characteristics

PARAMETER		TEST CONDITIONS[2]	V_{CC} (V)	25℃			-40℃ to 85℃		-55℃ to 125℃		UNIT
				MIN	TYP	MAX	MIN	MAX	MIN	MAX	
HC TYPES											
V_{IH}	High level input voltage		2	1.5			1.5		1.5		V
			4.5	3.15			3.15		3.15		V
			6	4.2			4.2		4.2		V
V_{IL}	Low level input voltage		2			0.5		0.5		0.5	V
			4.5			1.35		1.35		1.35	V
			6			1.8		1.8		1.8	V
V_{OH}	High level output voltage	I_{OH} = – 20 μA	2	1.9			1.9		1.9		V
		I_{OH} = – 20 μA	4.5	4.4			4.4		4.4		V
		I_{OH} = – 20 μA	6	5.9			5.9		5.9		V
	High level output voltage	I_{OH} = – 4 mA	4.5	3.98			3.84		3.7		V
		I_{OH} = – 5.2 mA	6	5.48			5.34		5.2		V
V_{OL}	Low level output voltage	I_{OL} = 20 μA	2			0.1		0.1		0.1	V
		I_{OL} = 20 μA	4.5			0.1		0.1		0.1	V
		I_{OL} = 20 μA	6			0.1		0.1		0.1	V
	Low level output voltage	I_{OL} = 4 mA	4.5			0.26		0.33		0.4	V
		I_{OL} = 5.2 mA	6			0.26		0.33		0.4	V
I_I	Input leakage current	V_I = V_{CC} or GND	6			±0.1		±1		±1	μA
I_{CC}	Supply current	V_I = V_{CC} or GND	6			8		80		160	μA
HCT TYPES											
V_{IH}	High level input voltage		4.5 to 5.5	2			2		2		V
V_{IL}	Low level input voltage		4.5 to 5.5			0.8		0.8		0.8	V
V_{OH}	High level output voltage	I_{OH} = – 20 μA	4.5	4.4			4.4		4.4		V
	High level output voltage	I_{OH} = – 4 mA	4.5	3.98			3.84		3.7		V
V_{OL}	Low level output voltage	I_{OL} = 20 μA	4.5			0.1		0.1		0.1	V
	Low level output voltage	I_{OL} = 4 mA	4.5			0.26		0.33		0.4	V
I_I	Input leakage current	V_I = V_{CC} or GND	5.5			±0.1		±1		±1	μA
I_{CC}	Supply current	V_I = V_{CC} or GND	5.5			8		80		160	μA

5.4 Electrical Characteristics (continued)

PARAMETER		TEST CONDITIONS(2)	V_{CC} (V)	25℃			-40℃ to 85℃		-55℃ to 125℃		UNIT
				MIN	TYP	MAX	MIN	MAX	MIN	MAX	
ΔI_{CC} (1)	Additional supply current per input pin	DS, D0-D7 inputs held at V_{CC} – 2.1 V	4.5 to 5.5		100	72		90		98	μA
		$\overline{PE}$ input held at V_{CC} – 2.1 V	4.5 to 5.5		100	126		157.5		171.5	
		CP, $\overline{CE}$ inputs held at V_{CC} – 2.1 V	4.5 to 5.5		100	180		225		245	
		$\overline{MR}$ inputs held at V_{CC} – 2.1 V	4.5 to 5.5		100	72		90		98	

(1) For dual-supply systems theoretical worst case (V_I = 2.4 V, V_{CC} = 5.5 V) specification is 1.8 mA.
(2) $V_I = V_{IH}$ or V_{IL}, unless otherwise noted.

5.5 Prerequisite for Switching Characteristics

See (Parameter Measurement Information)

PARAMETER		V_{CC} (V)	25℃		-40℃ to 85℃		-55℃ to 125℃		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	
HC TYPES									
f_{MAX}	Clock frequency	2	6		5		4		MHz
		4.5	30		25		20		MHz
		6	35		29		23		MHz
t_w	$\overline{MR}$ pulse width	2	100		125		150		ns
		4.5	20		25		30		ns
		6	17		21		26		ns
t_W	Clock pulse width	2	80		100		120		ns
		4.5	16		20		24		ns
		6	14		17		20		ns
t_{SU}	Set-up time Data and $\overline{CE}$ to clock	2	80		100		120		ns
		4.5	16		20		24		ns
		6	14		17		20		ns
t_H	Hold time data to clock	2	1		1		1		ns
		4.5	1		1		1		ns
		6	1		1		1		ns
t_{REM}	Removal time $\overline{MR}$ to clock	2	0		0		0		ns
		4.5	0		0		0		ns
		6	0		0		0		ns
t_{SU}	Set-up time $\overline{PE}$ to CP	2	145		180		220		ns
		4.5	29		36		44		ns
		6	25		31		38		ns
t_H	Hold time $\overline{PE}$ to CP or $\overline{CE}$	2	0		0		0		ns
		4.5	0		0		0		ns
		6	0		0		0		ns
HCT TYPES									
f_{MAX}	Clock frequency	4.5	25		20		16		MHz
t_w	$\overline{MR}$ pulse width	4.5	35		44		53		ns
t_w	Clock pulse width	4.5	20		25		30		ns

See (Parameter Measurement Information)

PARAMETER		V_{CC} (V)	25℃		-40℃ to 85℃		-55℃ to 125℃		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	
t_{SU}	Set-up time data and $\overline{CE}$ to clock	4.5	16		20		24		ns
t_H	Hold time data to clock	4.5	0		0		0		ns
t_{REM}	Removal time $\overline{MR}$ to clock	4.5	0		0		0		ns
t_{SU}	Set-up time $\overline{PE}$ to CP	4.5	30		38		45		ns
t_H	Hold time $\overline{PE}$ to CP or $\overline{CE}$	4.5	0		0		0		ns

5.6 Switching Characteristics

Input t_r, t_f = 6 ns. Unless otherwise specified, C_L = 50pF. See (Parameter Measurement Information)

PARAMETER		V_{CC} (V)	25℃		-40℃ to 85℃	-55℃ to 125℃	UNIT
			TYP	MAX	MAX	MAX	
HC TYPES							
t_{pd}	Clock to output	2		160	200	240	ns
		4.5	13(3)	32	40	48	ns
		6		27	34	41	ns
t_t	Output transition time	2		75	95	110	ns
		4.5		15	19	22	ns
		6		13	16	19	ns
t_{PHL}	Propagation delay MR to output	2		160	200	240	ns
		4.5		32	40	48	ns
		6		27	34	41	ns
C_I	Input capacitance			10	10	10	pF
C_{PD}	Power dissipation capacitance(1) (2)	5	41				pF
HCT TYPES							
t_{pd}	Clock to output	4.5		40	50	60	ns
t_t	Output transition time	4.5		15	19	22	ns
t_{PHL}	Propagation delay $\overline{MR}$ to output	4.5		40	50	60	ns
C_I	Input capacitance			10	10	10	pF

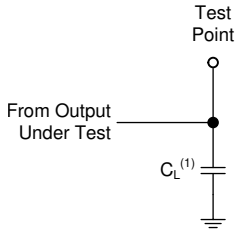
(1) C_{PD} is used to determine the dynamic power consumption, per gate.
(2) $P_D = C_{PD} V_{CC}^2 f_i + \Sigma (C_L V_{CC}^2 + f_O)$ where f_i = Input Frequency, f_O = Output Frequency, C_L = Output Load Capacitance, V_{CC} = Supply Voltage.
(3) C_L = 15 and V_{CC} = 5 V.

6 Parameter Measurement Information

Phase relationships between waveforms were chosen arbitrarily. All input pulses are supplied by generators having the following characteristics: PRR ≤ 1 MHz, Z_O = 50 Ω, t_t < 6 ns.

For clock inputs, f_{max} is measured when the input duty cycle is 50%.

The outputs are measured one at a time with one input transition per measurement.



(1) C_L includes probe and test-fixture capacitance.

图 6-1. Load Circuit for Push-Pull Outputs

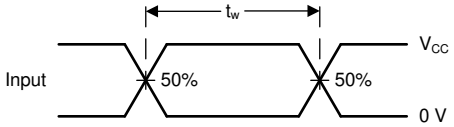


图 6-2. Voltage Waveforms, Standard CMOS Inputs Pulse Duration

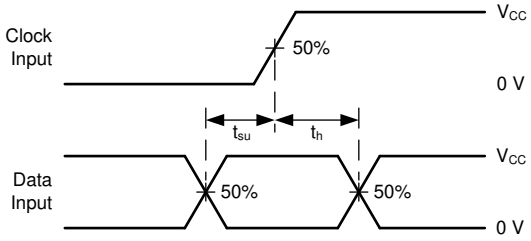
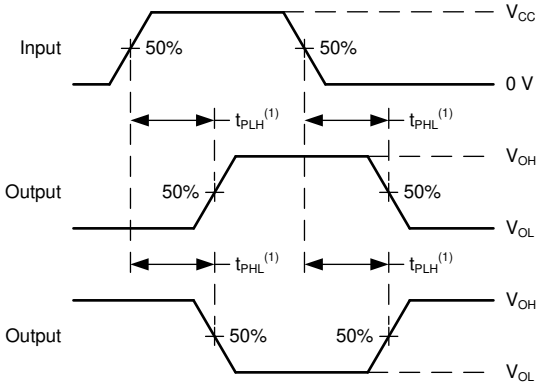
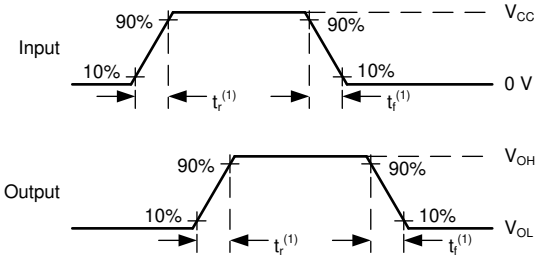


图 6-3. Voltage Waveforms, Standard CMOS Inputs Setup and Hold Times



(1) The greater between t_{PLH} and t_{PHL} is the same as t_{pd}.

图 6-4. Voltage Waveforms, Standard CMOS Inputs Setup Propagation Delays



(1) The greater between t_r and t_f is the same as t_t.

图 6-5. Voltage Waveforms, Input and Output Transition Times for Standard CMOS Input Devices

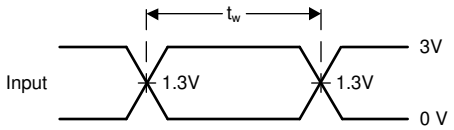


图 6-6. Voltage Waveforms, TTL-Compatible CMOS Inputs Pulse Duration

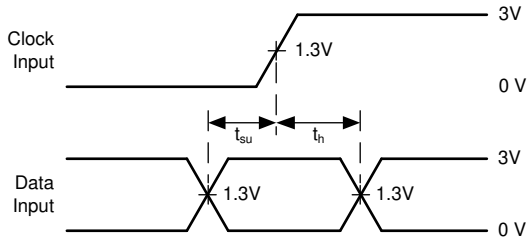
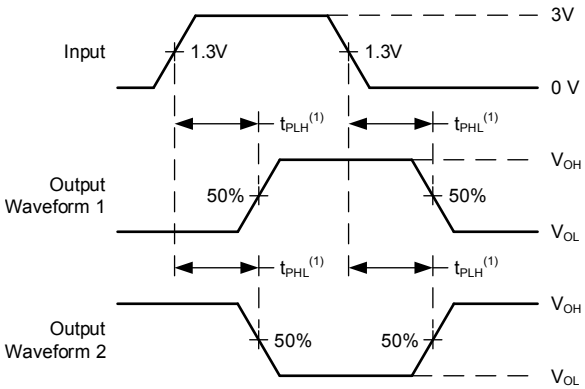


图 6-7. Voltage Waveforms, TTL-Compatible CMOS Inputs Setup and Hold Times



(1) The greater between t_{PLH} and t_{PHL} is the same as t_{pd}.

图 6-8. Voltage Waveforms, TTL-Compatible CMOS Inputs Propagation Delays

7 Detailed Description

7.1 Overview

The ’HC166 and ’HCT166 8-bit shift register is fabricated with silicon gate CMOS technology. It possesses the low power consumption of standard CMOS integrated circuits, and can operate at speeds comparable to the equivalent low power Schottky device.

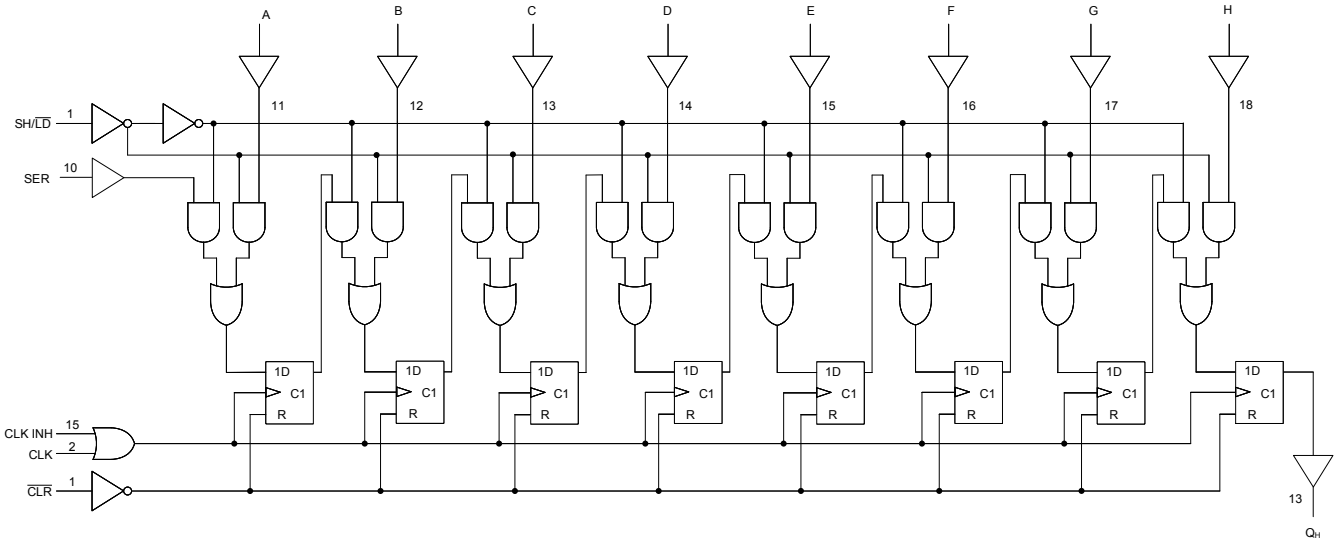
The ’HCT166 is functionally and pin compatible with the standard ’LS166.

The 166 is an 8-bit shift register that has fully synchronous serial or parallel data entry selected by an active LOW Parallel Enable ($\overline{PE}$) input. When the $\overline{PE}$ is LOW one setup time before the LOW-to-HIGH clock transition, parallel data is entered into the register. When $\overline{PE}$ is HIGH, data is entered into the internal bit position Q0 from Serial Data Input (DS), and the remaining bits are shifted one place to the right (Q0 → Q1 → Q2, etc.) with each positive-going clock transition. For expansion of the register in parallel to serial converters, the Q7 output is connected to the DS input of the succeeding stage.

The clock input is a gated OR structure which allows one input to be used as an active LOW Clock Enable ($\overline{CE}$) input. The pin assignment for the CP and $\overline{CE}$ inputs is arbitrary and can be reversed for layout convenience. The LOW-to-HIGH transition of $\overline{CE}$ input should only take place while the CP is HIGH for predictable operation.

A LOW on the Controller Reset ($\overline{MR}$) input overrides all other inputs and clears the register asynchronously, forcing all bit positions to a LOW state.

7.2 Functional Block Diagram



7.3 Device Functional Modes

表 7-1. Truth Table(1)

INPUTS						INTERNAL Q STATES		OUTPUT Q7
MASTER RESET	PARALLEL ENABLE	CLOCK ENABLE	CLOCK	SERIAL	PARALLEL D0 D7	Q0	Q1	
L	X	X	X	X	X	L	L	L
H	X	L	L	X	X	Q00	Q10	Q0
H	L	L	↑	X	a...h	a	b	h
H	H	L	↑	H	X	H	Q0n	Q6n
H	H	L	↑	L	X	L	Q0n	Q6n
H	X	H	↑	X	X	Q00	Q10	Q70

(1) H = High Voltage Level,
L = Low Voltage Level,
X = Don’t Care,
↑ = Transition from Low to High Level,
a...h = The level of steady-state input at inputs D0 thru D7, respectively,
Q00, Q10, Q70 = The level of Q0, Q1, or Q7, respectively, before the indicated steady-state input conditions were established
Q0n, Q6n = The level of Q0 or Q6, respectively, before the most recent ↑ transition of the clock.

8 Power Supply Recommendations

The power supply can be any voltage between the minimum and maximum supply voltage rating located in the *Recommended Operating Conditions*. Each V_{CC} terminal should have a good bypass capacitor to prevent power disturbance. A 0.1-μF capacitor is recommended for this device. It is acceptable to parallel multiple bypass caps to reject different frequencies of noise. The 0.1-μF and 1-μF capacitors are commonly used in parallel. The bypass capacitor should be installed as close to the power terminal as possible for best results.

9 Layout

9.1 Layout Guidelines

When using multiple-input and multiple-channel logic devices inputs must not ever be left floating. In many cases, functions or parts of functions of digital logic devices are unused; for example, when only two inputs of a triple-input AND gate are used or only 3 of the 4 buffer gates are used. Such unused input pins must not be left unconnected because the undefined voltages at the outside connections result in undefined operational states. All unused inputs of digital logic devices must be connected to a logic high or logic low voltage, as defined by the input voltage specifications, to prevent them from floating. The logic level that must be applied to any particular unused input depends on the function of the device. Generally, the inputs are tied to GND or V_{CC}, whichever makes more sense for the logic function or is more convenient.

10 Device and Documentation Support

TI offers an extensive line of development tools. Tools and software to evaluate the performance of the device, generate code, and develop solutions are listed below.

10.1 接收文档更新通知

要接收文档更新通知，请导航至 ti.com 上的器件产品文件夹。点击 *订阅更新* 进行注册，即可每周接收产品信息更改摘要。有关更改的详细信息，请查看任何已修订文档中包含的修订历史记录。

10.2 支持资源

TI E2E™ 支持论坛是工程师的重要参考资料，可直接从专家获得快速、经过验证的解答和设计帮助。搜索现有解答或提出自己的问题可获得所需的快速设计帮助。

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10.4 Electrostatic Discharge Caution

This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

10.5 术语表

TI 术语表　　本术语表列出并解释了术语、首字母缩略词和定义。

11 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

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邮寄地址：Texas Instruments, Post Office Box 655303, Dallas, Texas 75265

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
CD54HC166F3A	ACTIVE	CDIP	J	16	25	Non-RoHS & Green	SNPB	N / A for Pkg Type	-55 to 125	CD54HC166F3A	Samples
CD54HCT166F3A	ACTIVE	CDIP	J	16	25	Non-RoHS & Green	SNPB	N / A for Pkg Type	-55 to 125	CD54HCT166F3A	Samples
CD74HC166E	ACTIVE	PDIP	N	16	25	RoHS & Green	NIPDAU	N / A for Pkg Type	-55 to 125	CD74HC166E	Samples
CD74HC166M	OBSOLETE	SOIC	D	16		TBD	Call TI	Call TI	-55 to 125	HC166M	
CD74HC166M96	ACTIVE	SOIC	D	16	2500	RoHS & Green	NIPDAU | SN	Level-1-260C-UNLIM	-55 to 125	HC166M	Samples
CD74HCT166E	ACTIVE	PDIP	N	16	25	RoHS & Green	NIPDAU	N / A for Pkg Type	-55 to 125	CD74HCT166E	Samples
CD74HCT166EE4	ACTIVE	PDIP	N	16	25	RoHS & Green	NIPDAU	N / A for Pkg Type	-55 to 125	CD74HCT166E	Samples
CD74HCT166M	OBSOLETE	SOIC	D	16		TBD	Call TI	Call TI	-55 to 125	HCT166M	
CD74HCT166M96	ACTIVE	SOIC	D	16	2500	RoHS & Green	NIPDAU | SN	Level-1-260C-UNLIM	-55 to 125	HCT166M	Samples
CD74HCT166MT	OBSOLETE	SOIC	D	16		TBD	Call TI	Call TI	-55 to 125	HCT166M	

(1) The marketing status values are defined as follows:
ACTIVE: Product device recommended for new designs.
LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.
NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.
PREVIEW: Device has been announced but is not in production. Samples may or may not be available.
OBSOLETE: TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".
RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.
Green: TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

OTHER QUALIFIED VERSIONS OF CD54HC166, CD54HCT166, CD74HC166, CD74HCT166 :

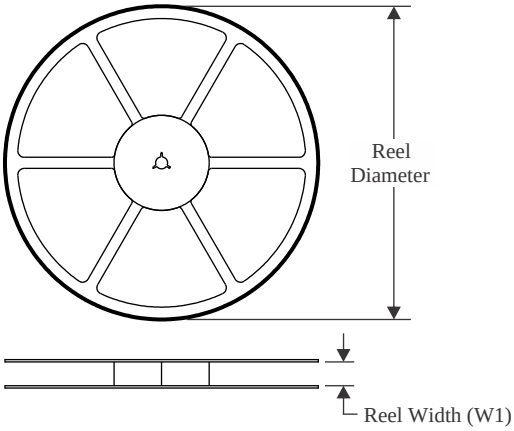
- Catalog : CD74HC166, CD74HCT166
- Military : CD54HC166, CD54HCT166

NOTE: Qualified Version Definitions:

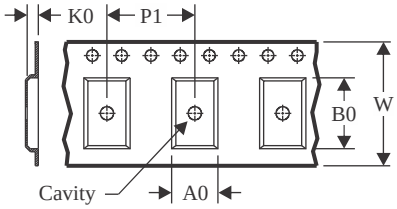
- Catalog - TI's standard catalog product
- Military - QML certified for Military and Defense Applications

TAPE AND REEL INFORMATION

REEL DIMENSIONS

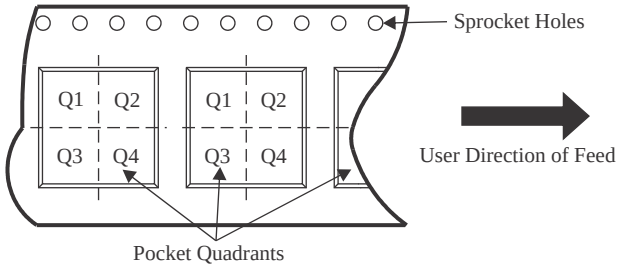


TAPE DIMENSIONS



A0	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

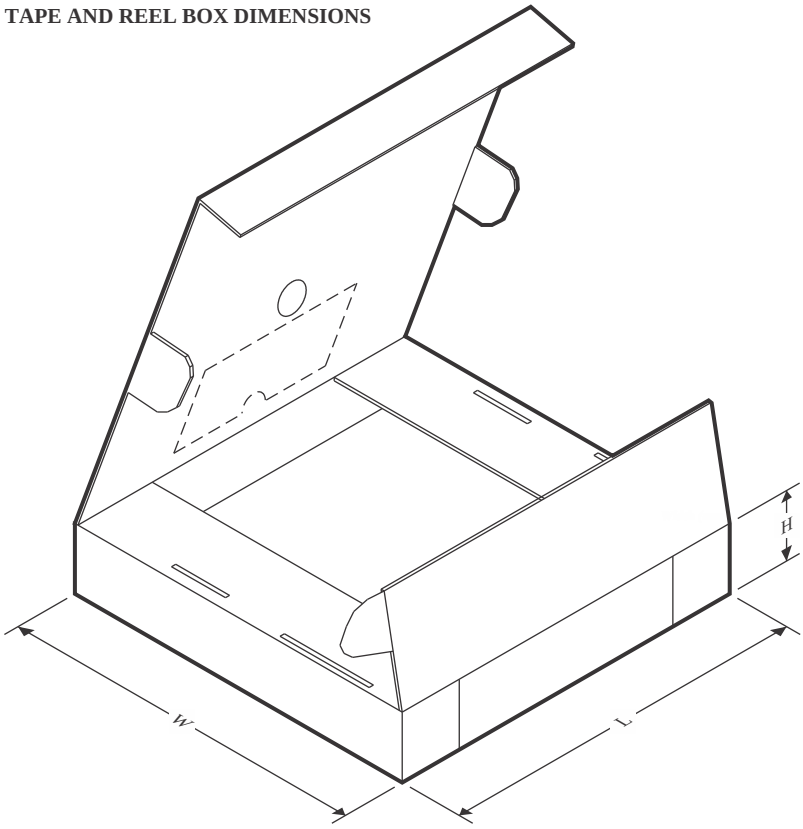
QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
CD74HC166M96	SOIC	D	16	2500	330.0	16.4	6.5	10.3	2.1	8.0	16.0	Q1
CD74HCT166M96	SOIC	D	16	2500	330.0	16.4	6.5	10.3	2.1	8.0	16.0	Q1

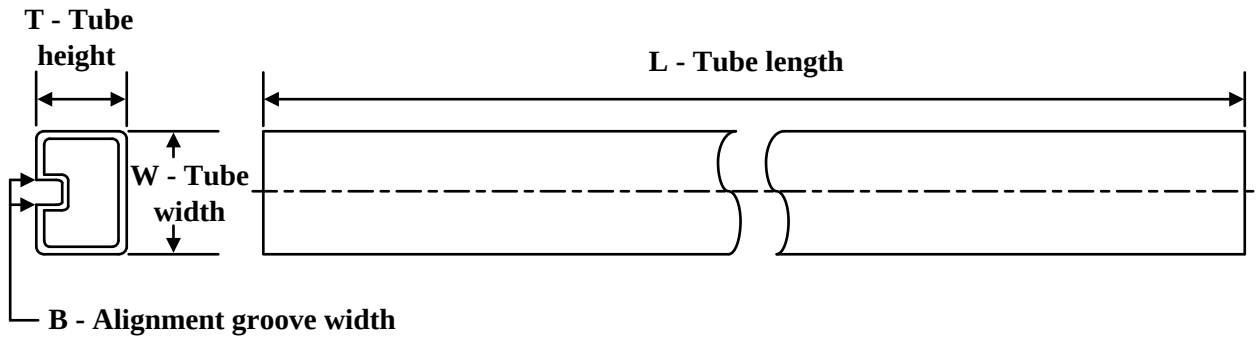
TAPE AND REEL BOX DIMENSIONS



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
CD74HC166M96	SOIC	D	16	2500	356.0	356.0	35.0
CD74HCT166M96	SOIC	D	16	2500	356.0	356.0	35.0

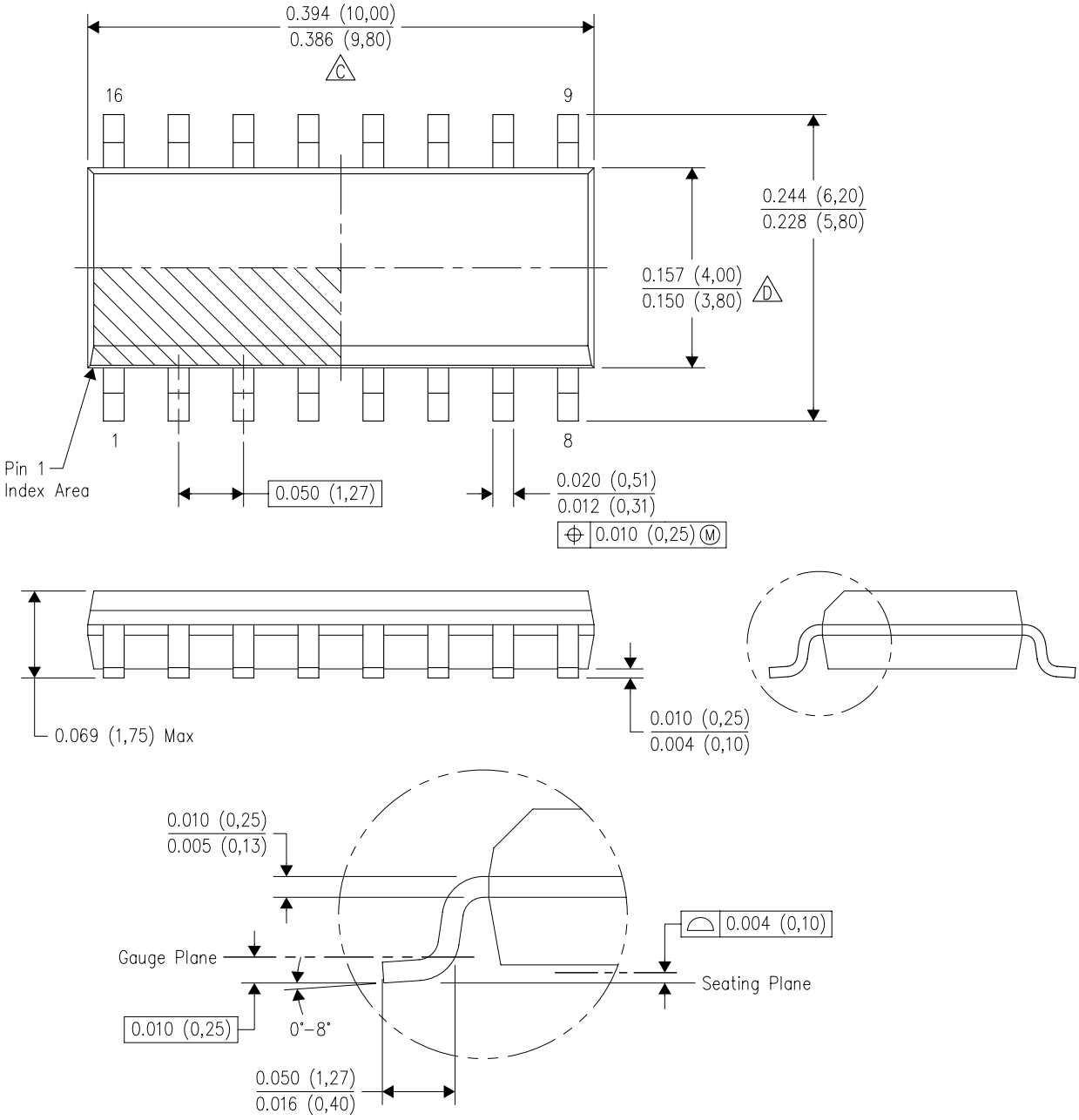
TUBE



*All dimensions are nominal

Device	Package Name	Package Type	Pins	SPQ	L (mm)	W (mm)	T (µm)	B (mm)
CD74HC166E	N	PDIP	16	25	506	13.97	11230	4.32
CD74HC166E	N	PDIP	16	25	506	13.97	11230	4.32
CD74HCT166E	N	PDIP	16	25	506	13.97	11230	4.32
CD74HCT166E	N	PDIP	16	25	506	13.97	11230	4.32
CD74HCT166EE4	N	PDIP	16	25	506	13.97	11230	4.32
CD74HCT166EE4	N	PDIP	16	25	506	13.97	11230	4.32

D (R–PDSO–G16) PLASTIC SMALL OUTLINE

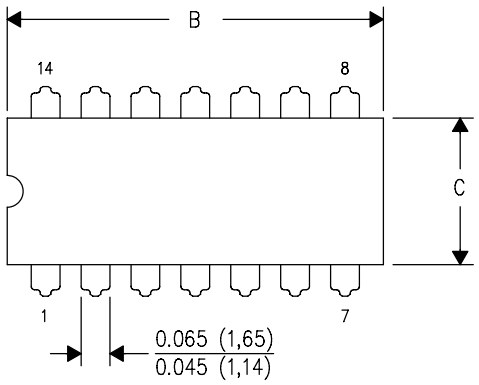


NOTES:
A. All linear dimensions are in inches (millimeters).
B. This drawing is subject to change without notice.
C. Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.006 (0,15) each side.
D. Body width does not include interlead flash. Interlead flash shall not exceed 0.017 (0,43) each side.
E. Reference JEDEC MS–012 variation AC.

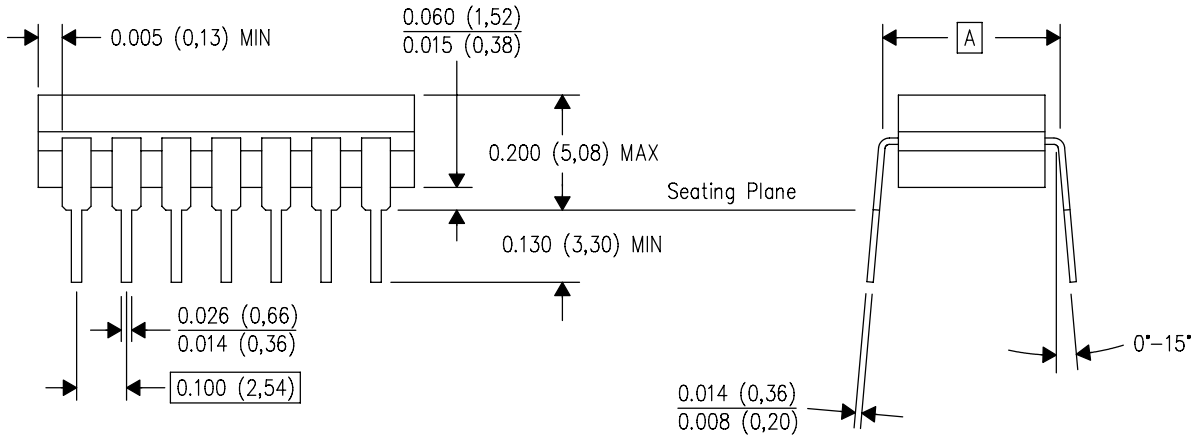
J (R–GDIP–T**)

14 LEADS SHOWN

CERAMIC DUAL IN–LINE PACKAGE



DIM \ PINS **	14	16	18	20
A	0.300 (7,62) BSC	0.300 (7,62) BSC	0.300 (7,62) BSC	0.300 (7,62) BSC
B MAX	0.785 (19,94)	.840 (21,34)	0.960 (24,38)	1.060 (26,92)
B MIN	—	—	—	—
C MAX	0.300 (7,62)	0.300 (7,62)	0.310 (7,87)	0.300 (7,62)
C MIN	0.245 (6,22)	0.245 (6,22)	0.220 (5,59)	0.245 (6,22)



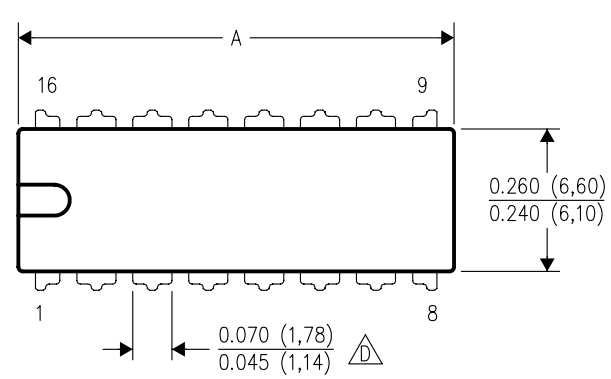
4040083/F 03/03

NOTES:
A. All linear dimensions are in inches (millimeters).
B. This drawing is subject to change without notice.
C. This package is hermetically sealed with a ceramic lid using glass frit.
D. Index point is provided on cap for terminal identification only on press ceramic glass frit seal only.
E. Falls within MIL STD 1835 GDIP1–T14, GDIP1–T16, GDIP1–T18 and GDIP1–T20.

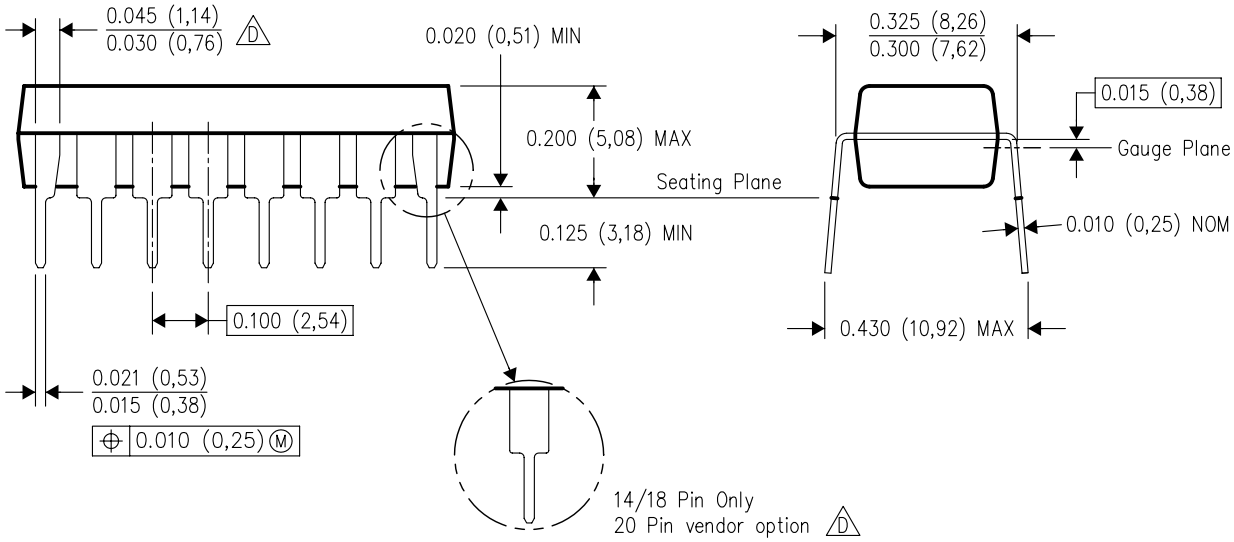
N (R–PDIP–T**)

PLASTIC DUAL–IN–LINE PACKAGE

16 PINS SHOWN



DIM \ PINS **	14	16	18	20
A MAX	0.775 (19,69)	0.775 (19,69)	0.920 (23,37)	1.060 (26,92)
A MIN	0.745 (18,92)	0.745 (18,92)	0.850 (21,59)	0.940 (23,88)
MS–001 VARIATION (C)	AA	BB	AC	AD



4040049/E 12/2002

NOTES:
A. All linear dimensions are in inches (millimeters).
B. This drawing is subject to change without notice.
C. Falls within JEDEC MS–001, except 18 and 20 pin minimum body length (Dim A).
D. The 20 pin end lead shoulder width is a vendor option, either half or full width.

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